	Туре	L#	Hits	Search Text	DBs	Time Stamp	o m m e	D ef	Er
1	BRS	L1	123	or resist or photoresist)) with ((first and second) near3 (layer or conductive))) and semiconductor) and @pd<=20000515) and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/15 20:03			0
2	BRS	L8	6997	(deposit\$3 or form\$3) with ((first adj (resist or photoresist or mask or pattern)) same (second adj (resist or photoresist or mask or pattern)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/15 20:10			0
3	BRS	L15	259	0 dila 210/4.0010.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/15 20:13			0
4	BRS	L22	2097	8 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/15 20:39			0
5	BRS	L29	4557	8 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/15 20:36			0
6	BRS	L36	2656	29 and @pd<=20000515	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/15 20:38	***************************************		0
7	BRS	L50	1043	36 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/15 20:13			0
8	BRS	L43	108	36 and 216/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/15 20:35			0

	Туре	L#	Hits	Search Text	DBs	Time Stamp	0 E E	ef in	Er ro
9	BRS	L57	3603	29 and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/15 20:37			0
10	BRS	L64	2719	57 and (metal or conduct\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/15 20:38			0
11	BRS	L71	1387	64 and @pd<=20000515	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/15 20:38			0
12	BRS	L85	2	78 and (microload\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/15 20:39			0
13	BRS	L78	716	71 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	191.90			0
14	BRS	L92	139	pattern\$3 same ((first and second) adj (metal or conduct\$3)) same ((first and second) adj (resist or photoresist))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/15 22:26			0
15	IS&R	L106	4	(("5492607") or ("4592132")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/16 00:10			0